BLM8G0710S-30PB; BLM8G0710S-30PBG

LDMOS 2-stage power MMIC

Rev. 2 — 1 July 2015 Product data sheet

1. Product profile

1.1 General description

The BLM8G0710S-30PB(G) is a dual section, 2-stage power MMIC using NXP's state of the art GEN8 LDMOS technology. This multiband device is perfectly suited as general purpose driver or small cell final in the frequency range from 700 MHz to 1000 MHz. Available in gull wing or straight lead outline.

Table 1. Performance

Typical RF performance at T_{case} = 25 °C; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA.
Test signal: 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF; per section unless otherwise specified in a class-AB production circuit.

Test signal	f	V_{DS}	$P_{L(AV)}$	G_p	η_D	$ACPR_{5M}$
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
single carrier W-CDMA	957.5	28	3	35	27	–41.5

1.2 Features and benefits

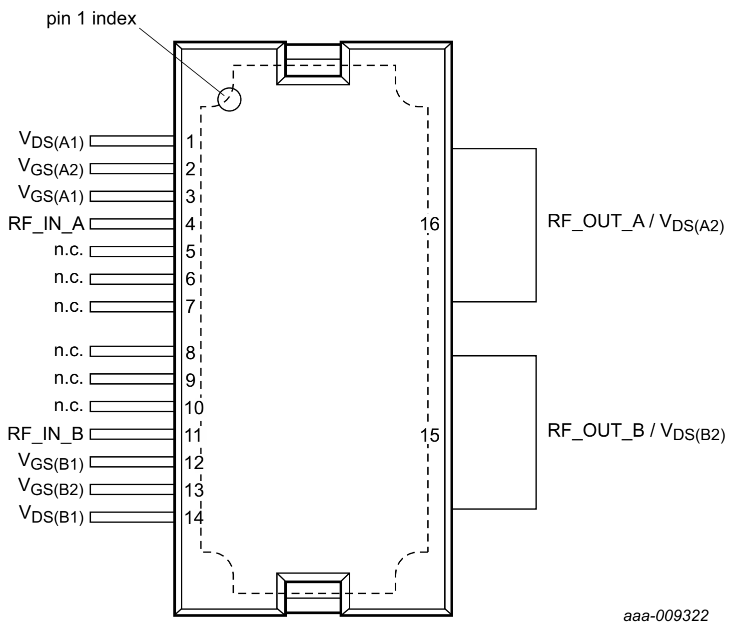
- Designed for broadband operation (frequency 700 MHz to 1000 MHz)
- High section-to-section isolation enabling multiple combinations
- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

- RF power MMIC for W-CDMA base stations in the 700 MHz to 1000 MHz frequency range. Possible circuit topologies are the following as also depicted in Section 8.1:
  - Dual section or single ended
  - Doherty
  - Quadrature combined
  - Push-pull

2. Pinning information

2.1 Pinning



Transparent top view

The exposed backside of the package is the ground terminal of the device.

Fig 1. Pin configuration

2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$V_{DS(A1)}$	1	drain-source voltage of driver stage A1
$V_{GS(A2)}$	2	gate-source voltage of final stage A2
$V_{GS(A1)}$	3	gate-source voltage of driver stage A1
RF_IN_A	4	RF input section A
n.c.	5	not connected
n.c.	6	not connected
n.c.	7	not connected
n.c.	8	not connected
n.c.	9	not connected
n.c.	10	not connected
RF_IN_B	11	RF input section B
$V_{GS(B1)}$	12	gate-source voltage of driver stage B1
$V_{GS(B2)}$	13	gate-source voltage of final stage B2
$V_{DS(B1)}$	14	drain-source voltage of driver stage B1

Table 2. Pin description *...continued*

Symbol	Pin	Description
RF_OUT_B/$V_{DS(B2)}$	15	RF output section B / drain-source voltage of final stage B2
RF_OUT_A/$V_{DS(A2)}$	16	RF output section A / drain-source voltage of final stage A2
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLM8G0710S-30PB	HSOP16F	plastic, heatsink small outline package; 16 leads (flat)	SOT1211-2
BLM8G0710S-30PBG	HSOP16	plastic, heatsink small outline package; 16 leads	SOT1212-2

4. Block diagram

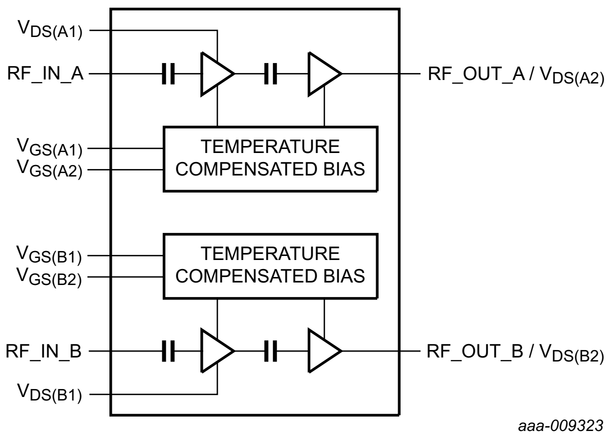


Fig 2. Block diagram

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+13	V
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature	[1]	-	225	°C
T_{case}	case temperature		-	150	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics
Measured for total device.

Symbol	Parameter	Conditions		Value	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	final stage; T_{case} = 90 °C; P_L = 2.52 W	[1]	1.5	K/W
		driver stage; T_{case} = 90 °C; P_L = 2.52 W	[1]	5.3	K/W

[1] When operated with a CW signal.

7. Characteristics

Table 6. DC characteristics
T_{case} = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Final stage							
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.241 mA		65	-	-	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 120 mA		1.5	2	2.7	V
		V_{DS} = 28 V; I_D = 120 mA	[1]	1.9	2.6	3.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V		-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = 5.65 V; V_{DS} = 10 V		-	4.4	-	A
I_{GSS}	gate leakage current	V_{GS} = 1.0 V; V_{DS} = 0 V		-	-	140	nA
Driver stage							
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.06 mA		65	-	-	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 30 mA		1.5	2.1	2.7	V
		V_{DS} = 28 V; I_D = 30 mA	[2]	1.9	2.6	3.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V		-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = 5.65 V; V_{DS} = 10 V		-	1.1	-	A
I_{GSS}	gate leakage current	V_{GS} = 1.0 V; V_{DS} = 0 V		-	-	140	nA

[1] In production circuit with 1.3 kΩ gate feed resistor.

[2] In production circuit with 1.2 kΩ gate feed resistor.

Table 7. RF Characteristics
Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; $P_{L(AV)}$ = 3 W. Per section unless otherwise specified, measured in a NXP wideband f = 700 MHz to 1000 MHz production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Test signal: single carrier W-CDMA [1]						
G_p	power gain	f = 730.5 MHz	-	35.7	-	dB
		f = 957.5 MHz	33.5	35	36.5	dB
η_D	drain efficiency	f = 730.5 MHz	-	24	-	%
		f = 957.5 MHz	23.5	27	-	%
RL_{in}	input return loss	f = 730.5 MHz	-	–20	-	dB
		f = 957.5 MHz	-	–16	–10	dB
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	f = 730.5 MHz	-	–39	-	dBc
		f = 957.5 MHz	-	–41.5	–38.5	dBc

Table 7. RF Characteristics *...continued*

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; $P_{L(AV)}$ = 3 W. Per section unless otherwise specified, measured in a NXP wideband f = 700 MHz to 1000 MHz production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	f = 730.5 MHz	-	8	-	dB
		f = 957.5 MHz	7.3	8	-	dB
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with temperature	T = –40 °C to +85 °C				
		final stage I_{Dq}; gate feed resistor = 1.3 kΩ	-	0.5	-	%
		driver stage I_{Dq}; gate feed resistor = 1.2 kΩ	-	0.5	-	%
Test signal: CW [2]						
$\Delta\varphi_{s21}$	phase response difference	between sections	–10	-	+10	deg
$\Delta\|s_{21}\|^2$	insertion power gain difference	between sections	–0.5	-	+0.5	dB

[1] 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF.

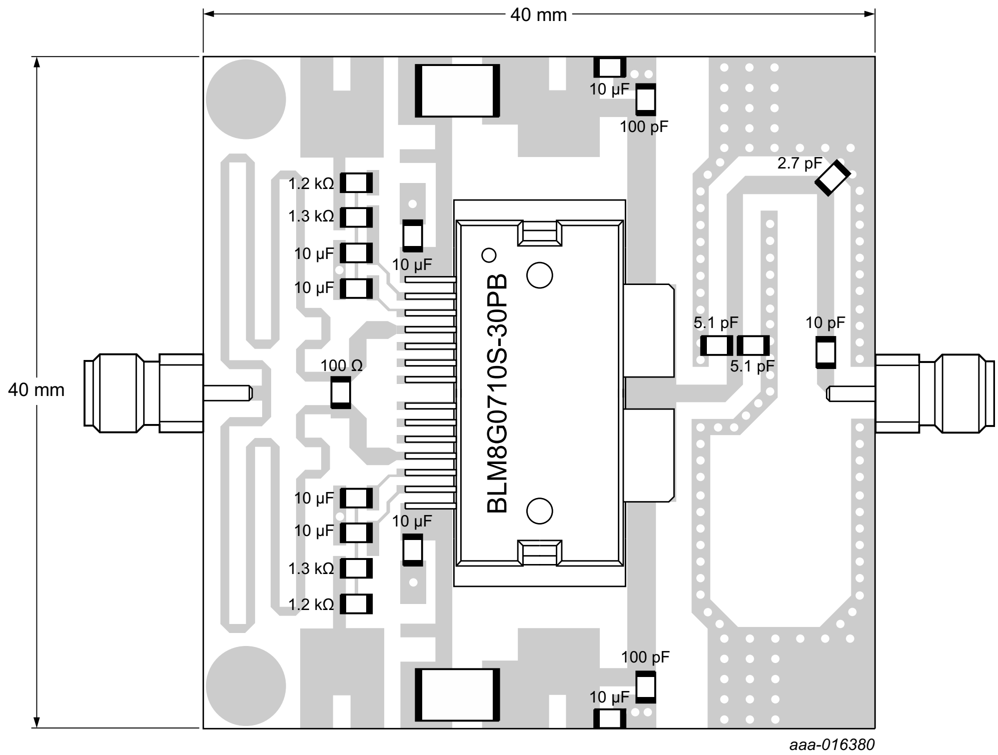
[2] f = 957.5 MHz.

8. Application information

Table 8. Typical performance

Test signal: 1-tone CW; RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 60 mA (both sections); I_{Dq2} = 240 mA (both sections) unless otherwise specified, measured in a NXP wideband f = 700 MHz to 1000 MHz class AB application circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(1dB)}$	output power at 1 dB gain compression	f = 800 MHz	-	29.7	-	W
η_D	drain efficiency	at $P_{L(1dB)}$; f = 800 MHz	-	51.7	-	%
G_p	power gain	$P_{L(AV)}$ = 8 W; f = 800 MHz	-	35.8	-	dB
B_{video}	video bandwidth	2-tone CW; $P_{L(AV)}$ = 16 W; f = 881 MHz	-	168	-	MHz
G_{flat}	gain flatness	$P_{L(AV)}$ = 8 W	-	0.5	-	dB
$\Delta G/\Delta T$	gain variation with temperature	f = 800 MHz	-	0.03	-	dB/°C
$\|s_{12}\|^2$	isolation	between sections A and B; $P_{L(AV)}$ = 8 W; f = 800 MHz	-	26	-	dB
K	Rollett stability factor	T = –40 °C; f = 0.1 GHz to 3 GHz	-	>1	-	



Printed-Circuit Board (PCB): Rogers 4350; thickness = 0.508 mm.

Fig 3. Component layout for class-AB application circuit

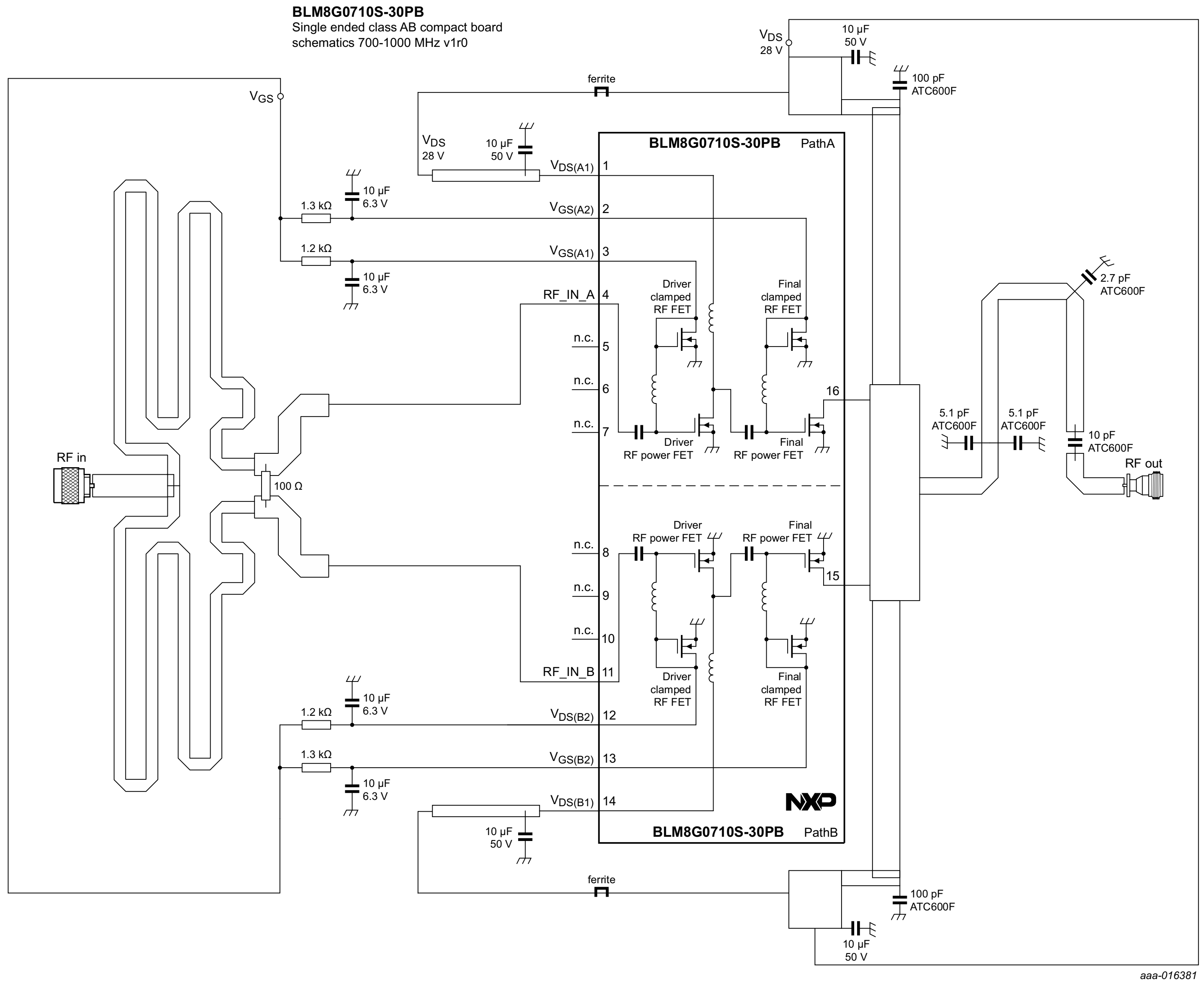


Fig 4. Electrical schematic

8.1 Possible circuit topologies

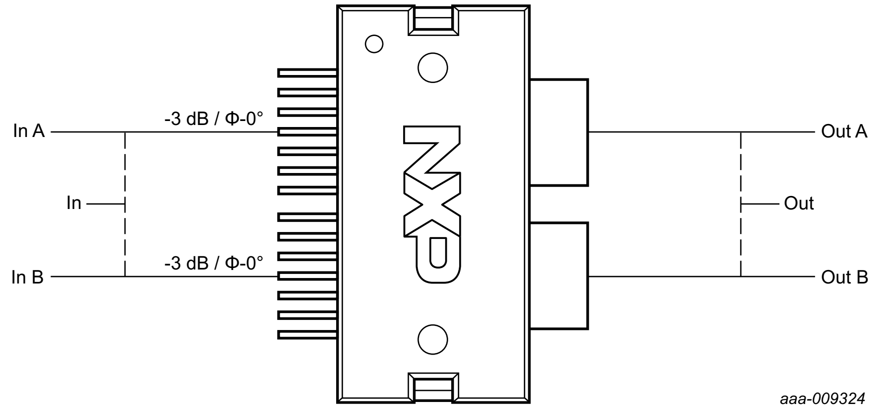


Fig 5. Dual section or single ended

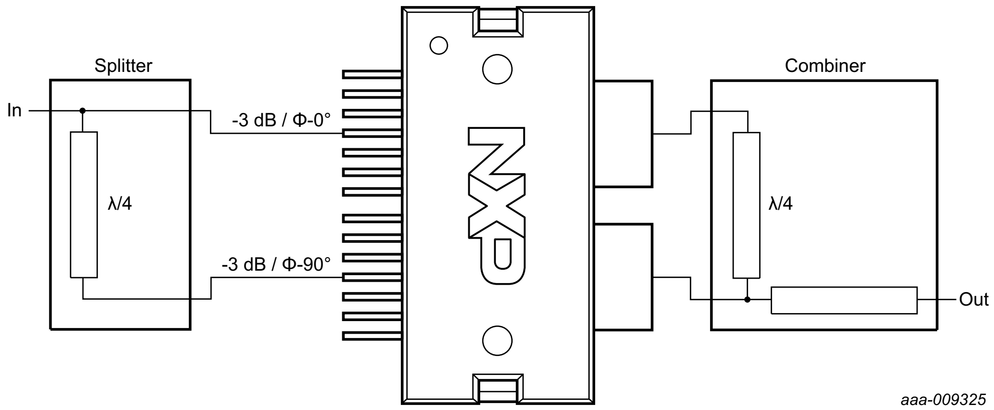


Fig 6. Doherty

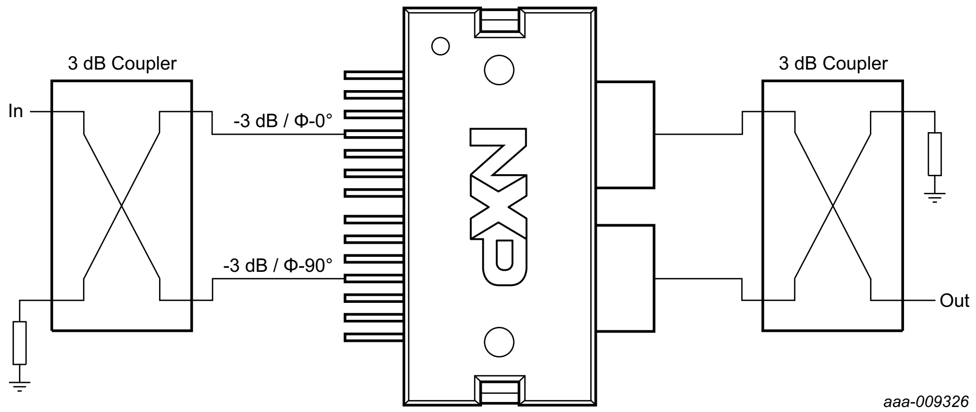


Fig 7. Quadrature combined

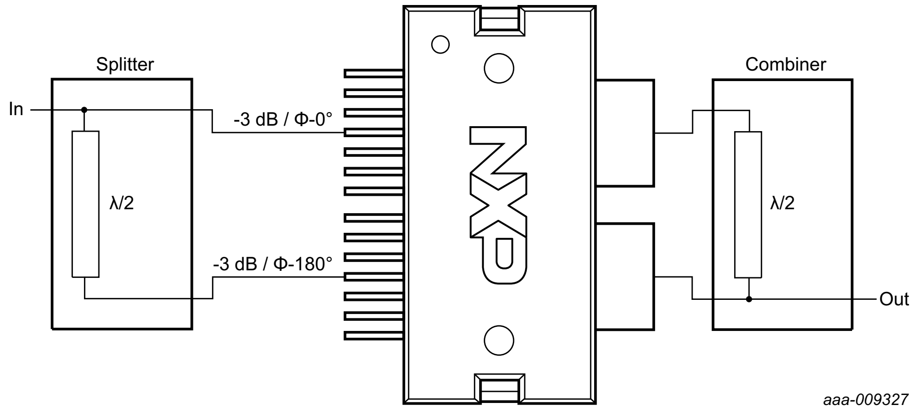


Fig 8. Push-pull

8.2 Ruggedness in class-AB operation

The BLM8G0710S-30PB and BLM8G0710S-30PBG are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq1} = 40 mA; I_{Dq2} = 120 mA; P_i = 13 dBm, P_i is measured at CW and corresponding to $P_{L(3dB)}$ under Z_S = 50 Ω; f = 840 MHz.

8.3 Impedance information

Table 9. Typical impedance tuned for maximum output power

Measured load-pull data per section; test signal: pulsed CW; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; t_p = 100 μs; δ = 10 %; Z_S = 50 Ω. Typical values unless otherwise specified.

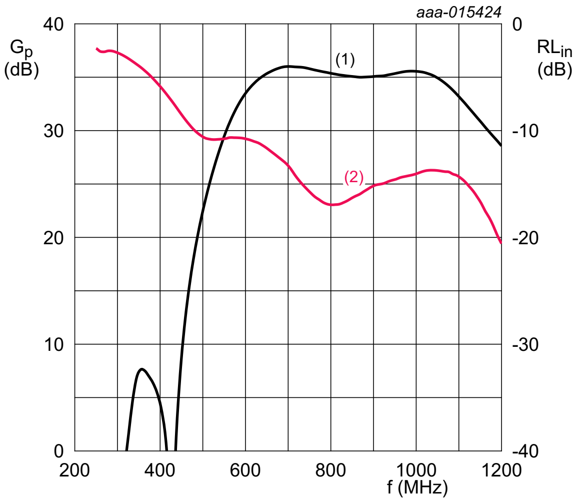
f	at 1dB gain compression point					at 3dB gain compression point				
	Z_L	$G_{p(max)}$	P_L	η_{add}	AM-PM conversion	Z_L	$G_{p(max)}$	P_L	η_{add}	AM-PM conversion
(MHz)	(Ω)	(dB)	(W)	(%)	(deg)	(Ω)	(dB)	(W)	(%)	(deg)
BLM8G0710S-30PB										
680	6.1 + j5.1	34.2	44	56.2	–7.3	6.4 + j4.3	34	44.9	59.4	–9.2
700	5.6 + j4.6	34	43.9	53.3	–6.8	6.2 + j3.6	33.9	44.8	56.4	–8.5
720	6.1 + j5.2	34.5	43.8	56.7	–6.4	6.2 + j3.7	34	44.8	56.8	–8
740	5.7 + j4.6	34.1	43.8	53.7	–5.3	6.3 + j3.6	33.9	44.8	57.2	–7.2
760	5.7 + j4.5	34	43.8	54.6	–4.4	6.3 + j3.5	33.8	44.8	57.4	–6.1
780	6.2 + j3.5	33.6	43.8	53.4	–3.6	6.2 + j3.5	33.6	44.8	57.7	–6.2
800	7.0 + j3.3	33.7	43.9	55.6	–2.6	6.2 + j2.8	33.4	44.9	56.3	–5
820	6.3 + j2.9	33.3	43.9	52.7	–3	6.3 + j2.9	33.3	44.8	56.8	–5.7
840	6.3 + j2.8	33.2	43.9	53.3	–2.1	6.8 + j2.2	33.1	44.9	56.5	–4.1
860	7.0 + j3.2	33.5	43.8	56	–2.2	7.4 + j1.7	33.1	44.8	56.2	–4
880	6.7 + j2.1	33.1	43.8	52	–1.3	7.4 + j1.7	33.1	44.8	56.2	–3.3
900	7.4 + j1.8	33.2	43.9	53.4	–1.2	7.2 + j0.9	32.9	44.8	54.3	–3.4
920	6.8 + j2.2	33.3	43.8	53.1	–1	7.3 + j0.9	32.9	44.7	54.2	–2.7
940	7.5 + j1.7	33.4	43.8	53.1	–0.5	8.1 + j0.7	33.2	44.7	55.2	–2
960	7.2 + j0.9	33.2	43.6	49.7	–0.2	7.2 + j0.9	33.2	44.6	53.4	–2.4
980	6.5 + j1.3	33.2	43.7	49.7	–0.3	8.0 + j0.8	33.4	44.7	55.1	–2
1000	8.1 + j0.9	33.4	43.6	51.4	0.3	8.1 + j0.9	33.4	44.6	55.1	–2.2
BLM8G0710S-30PBG										
700	5.7 + j4.6	34.7	43.5	53.5	–7.3	6.4 + j3.1	34.4	44.4	55.3	–8.8
720	5.8 + j3.8	34.6	43.5	52.1	–6	6.3 + j3.4	34.6	44.4	56.6	–8.3
740	5.6 + j3.8	34.5	43.5	51.7	–6.2	6.5 + j2.6	34.4	44.5	55.5	–7.6
760	6.1 + j3.2	34.3	43.5	52.5	–5	7.4 + j1.8	34.2	44.5	55.9	–6
780	5.7 + j2.7	33.8	43.5	50.1	–4.1	6.5 + j1.6	33.6	44.5	53.1	–5.5
800	6.4 + j2.2	33.7	43.7	52.7	–3.1	7.1 + j1.3	33.6	44.7	55.7	–4.8
820	6.8 + j2.4	33.8	43.7	54.3	–2.6	6.4 + j1.2	33.3	44.7	54.2	–4.8
840	7.0 + j0.8	33.3	43.7	51.2	–2.3	7.0 + j0.8	33.3	44.7	55	–4.7
860	6.8 + j1.9	33.6	43.6	53.2	–2.5	7.5 + j0.5	33.3	44.6	54.7	–4.4
880	6.6 + j1.3	33.5	43.5	50.8	–2	7.4 + j0.7	33.4	44.5	54.6	–4.3
900	7.1 + j1.3	33.7	43.4	51.6	–1.2	8.2 + j0.3	33.6	44.4	54.8	–2.9
920	7.4 + j0.0	33.4	43.4	49.4	–0.7	7.4 + j0.1	33.4	44.5	53.8	–2.8
940	8.0 – j0.2	33.4	43.3	49.3	–0.2	8.0 + j0.1	33.5	44.4	53.9	–2.4
960	7.8 + j0.7	34	43.3	51.1	0.1	7.9 – j0.6	33.5	44.3	52.4	–2
980	7.7 – j0.5	33.7	43.3	48.6	0.5	7.7 – j0.5	33.7	44.4	53	–1.6
1000	7.2 – j0.4	33.5	43.3	48.4	0.1	7.2 – j0.4	33.5	44.3	52.7	–2.3

Table 10. Typical impedance tuned for maximum power added efficiency

Measured load-pull data per section; test signal: pulsed CW; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; t_p = 100 μs; δ = 10 %; Z_S = 50 Ω. Typical values unless otherwise specified.

	at 1dB gain compression point					at 3dB gain compression point				
f	Z_L	$G_{p(max)}$	P_L	η_{add}	AM-PM conversion	Z_L	$G_{p(max)}$	P_L	η_{add}	AM-PM conversion
(MHz)	(Ω)	(dB)	(W)	(%)	(deg)	(Ω)	(dB)	(W)	(%)	(deg)
BLM8G0710S-30PB										
680	9.6 + j9.3	35.5	42.6	65.9	–8.9	9.3 + j8.4	35.3	43.6	68.1	–11.1
700	8.7 + j9.5	35.6	42.5	65.4	–9	9.2 + j8.5	35.5	43.5	67.3	–10.7
720	8.8 + j9.6	35.7	42.3	64.5	–8	8.8 + j9.6	35.7	43	67	–11
740	8.0 + j9.5	35.6	42.3	64.2	–7.3	8.5 + j8.7	35.4	43.3	66.7	–9.7
760	8.9 + j9.4	35.5	42.3	64.5	–5.5	9.4 + j8.4	35.3	43.3	66.7	–7.3
780	8.4 + j8.5	35.1	42.5	63.8	–5	8.4 + j8.5	35.1	43.2	66.1	–8.2
800	8.4 + j8.6	35.1	42.4	63.5	–4.2	9.2 + j8.5	35.1	43.2	65.4	–6.1
820	8.4 + j8.7	34.9	42.3	62.7	–4.1	8.7 + j6.8	34.6	43.7	65.1	–6.3
840	8.5 + j8.6	34.9	42.3	63	–3.1	7.9 + j6.9	34.6	43.7	65.1	–6.2
860	8.5 + j8.5	34.8	42.2	62.1	–2.9	7.9 + j6.8	34.5	43.7	64.5	–6.2
880	7.6 + j8.5	34.8	42.1	61.8	–3	7.8 + j6.8	34.5	43.6	64	–5.3
900	8.0 + j7.7	34.7	42.4	61.9	–2.3	7.8 + j6.8	34.6	43.5	63.8	–5.2
920	8.7 + j6.8	34.6	42.7	61.2	–1	8.1 + j7.8	34.8	43.1	63.1	–3.9
940	8.2 + j7.7	34.9	42.2	60.6	–1.3	8.3 + j5.9	34.6	43.7	62.4	–2.8
960	7.9 + j6.8	34.9	42.4	59.3	–1.1	8.7 + j6.7	34.8	43.3	61.8	–1.9
980	7.5 + j8.5	35.2	41.7	59.8	–1	8.6 + j6.8	34.8	43.3	62.1	–1.5
1000	8.0 + j7.8	35	41.9	59.1	–0.2	7.1 + j6.8	34.9	43.1	61.6	–3.2
BLM8G0710S-30PBG										
700	8.4 + j8.2	36	42.3	63.4	–9	8.5 + j8.5	36.1	42.9	65.8	–12.7
720	8.6 + j9.1	36.2	41.9	63.9	–8.1	8.9 + j8.8	36.1	42.8	66.8	–11
740	8.3 + j8.2	36	42.2	62.6	–7.6	8.3 + j8.2	36	42.9	65.4	–10.9
760	9.6 + j7.7	35.7	42.2	62.2	–5.4	8.8 + j8.7	35.9	42.6	65.1	–9.2
780	8.5 + j7.1	35.4	42.4	61.5	–5.1	7.3 + j8.1	35.5	42.7	64.2	–10.2
800	8.0 + j8.3	35.5	41.8	62.1	–4.8	7.1 + j8.0	35.5	42.8	64.9	–9.7
820	8.0 + j7.1	35.1	42.3	61.6	–4	8.3 + j8.2	35.3	42.6	64	–6.9
840	8.8 + j7.2	35.1	42.1	61.4	–3.4	8.1 + j8.1	35.3	42.5	63.5	–7
860	8.4 + j7.1	35.1	42.1	60.9	–3.3	8.4 + j7.1	35.1	42.9	63.4	–6
880	8.1 + j6.4	35.1	42.2	60.1	–2.9	8.2 + j7.4	35.3	42.7	62.3	–6
900	7.3 + j6.2	35.2	42.1	59.5	–2.8	8.0 + j7.2	35.4	42.6	62.1	–4.9
920	8.0 + j7.4	35.4	41.6	59.5	–2.1	7.3 + j6.3	35.3	42.9	61.8	–5.4
940	8.1 + j6.6	35.3	41.8	58.7	–1.5	6.8 + j6.5	35.4	42.6	60.9	–5.7
960	9.5 + j5.4	35.2	42.2	57.8	0	7.0 + j6.9	35.8	42.4	60.5	–4.2
980	8.1 + j6.5	35.4	41.7	58.1	–0.3	7.1 + j6.3	35.5	42.6	61.3	–3
1000	6.9 + j4.9	35	42.2	58.2	–1.1	7.0 + j6.0	35.2	42.7	61.1	–3.2

8.4 Graphs

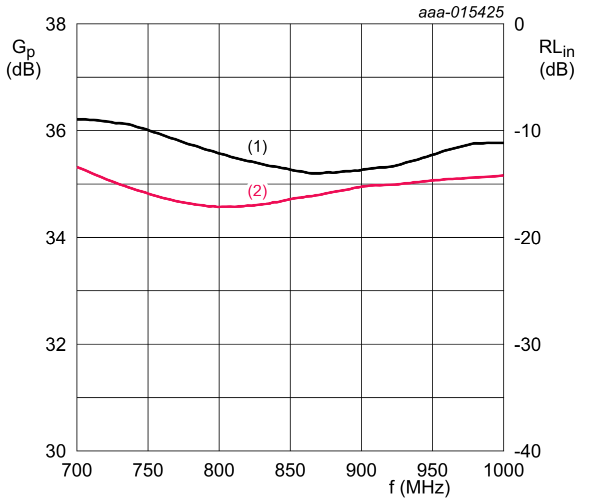


T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; P_L = 0.25 W. Per section.

(1) magnitude of G_p

(2) magnitude of RL_{in}

Fig 9. Wideband power gain and input return loss as function of frequency; typical values

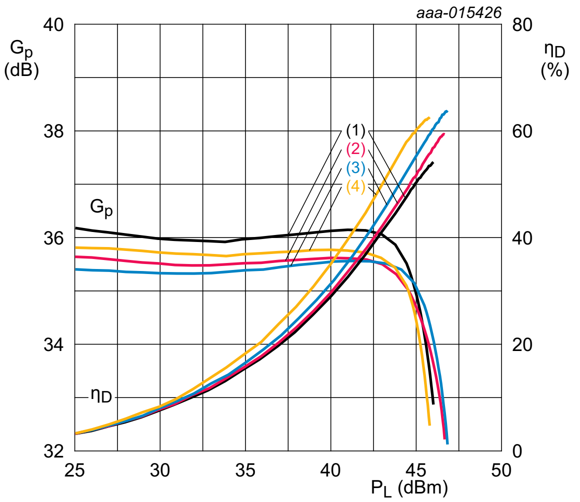


T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; P_L = 0.25 W. Per section.

(1) magnitude of G_p

(2) magnitude of RL_{in}

Fig 10. In-band power gain and input return loss as function of frequency; typical values



T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA. Per section.

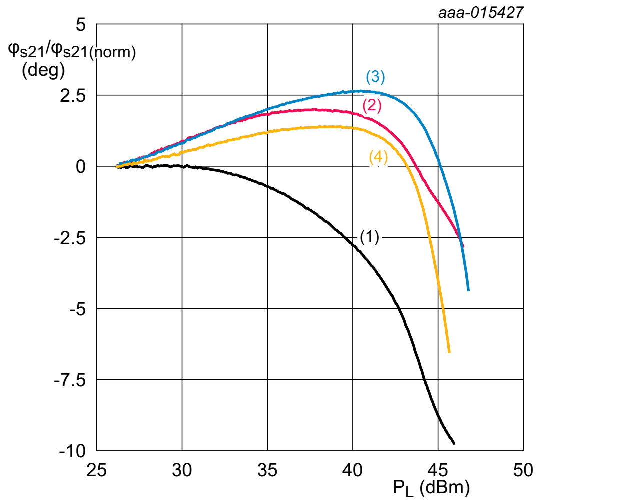
(1) f = 700 MHz

(2) f = 800 MHz

(3) f = 900 MHz

(4) f = 1000 MHz

Fig 11. Power gain and drain efficiency as function of output power; typical values



Normalized at P_L = 26 dBm; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA. Per section.

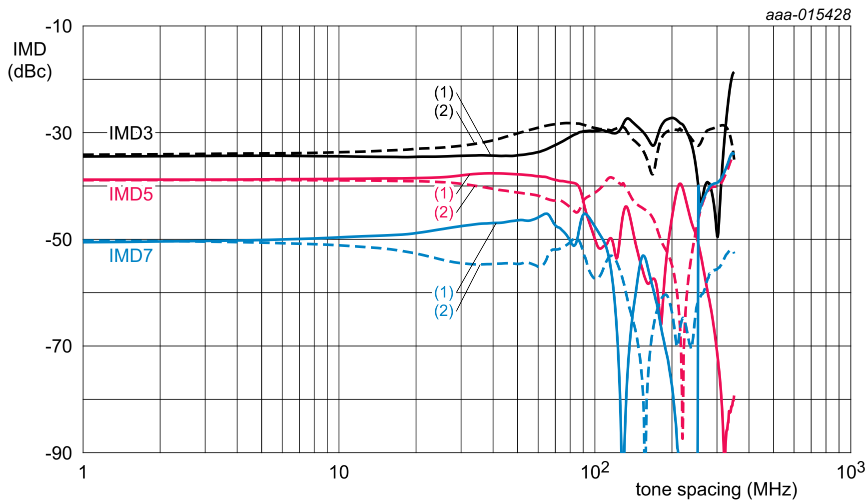
(1) f = 700 MHz

(2) f = 800 MHz

(3) f = 900 MHz

(4) f = 1000 MHz

Fig 12. Normalized phase response as a function of output power; typical values

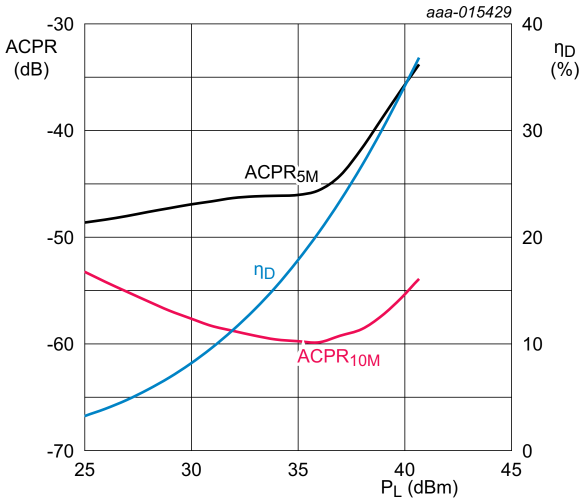


T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; f = 881 MHz; 2-tone CW; P_L = 8 W. Per section.

(1) IMD low

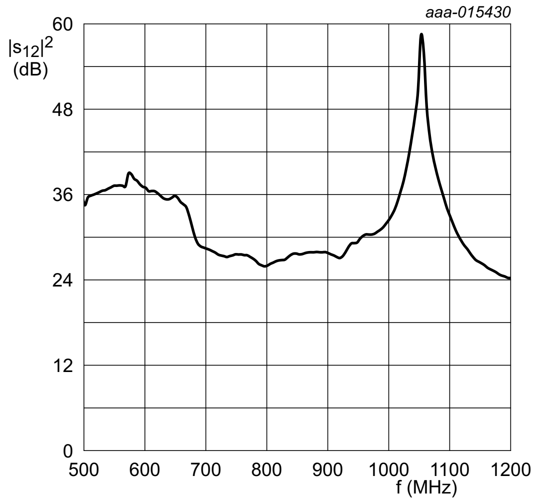
(2) IMD high

Fig 13. Intermodulation distortion as a function of tone spacing; typical values



T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; f = 900 MHz; 1-carrier W-CDMA; test model 1; PAR = 9.9 dB at 0.01 % probability on CCDF. Per section.

Fig 14. Adjacent channel power ratio and drain efficiency as function of output power; typical values

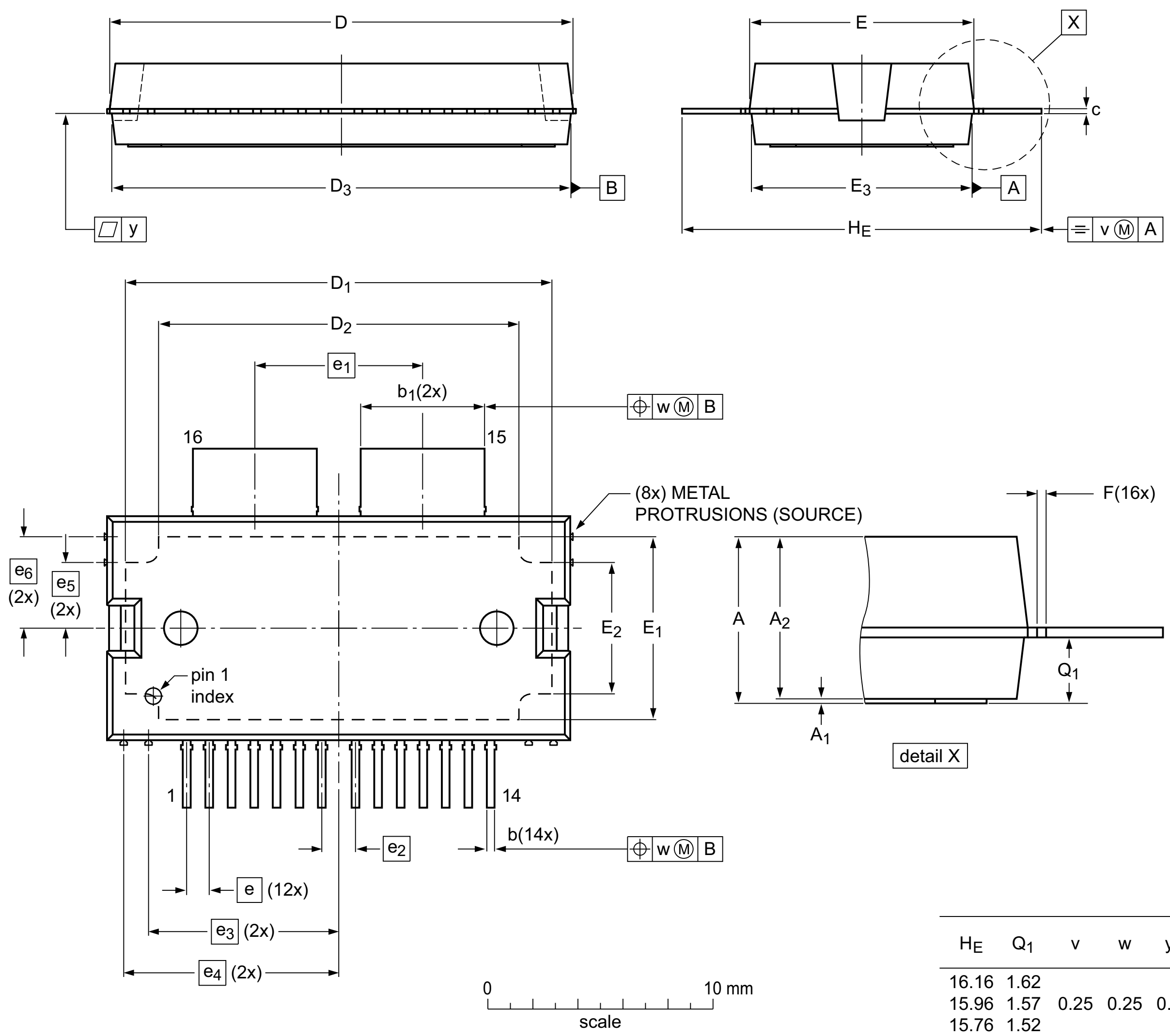


T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 30 mA; I_{Dq2} = 120 mA; measured on evaluation board.

Fig 15. Isolation as a function of frequency; typical values

9. Package outline

HSOP16F: plastic, heatsink small outline package; 16 leads(flat) **SOT1211-2**



H_E	Q_1	v	w	y
16.16	1.62			
15.96	1.57	0.25	0.25	0.1
15.76	1.52			

Dimensions (mm are the original dimensions)

Unit		A	A_1	A_2	b	b_1	c	D(1)	D_1	D_2	D_3	E(1)	E_1	E_2	E_3	e	e_1	e_2	e_3	e_4	e_5	e_6	F
	max	3.9	0.2	3.65	0.40	5.55	0.27	20.62	19.00	16.05	20.44	10.01	8.18	5.89	9.83								
mm	nom		0.1	3.60	0.35	5.50	0.22	20.57	18.95	16.00	20.39	9.96	8.13	5.84	9.78	1.0	7.45	1.5	8.45	9.55	2.97	4.07	0.2
	min		0	3.55	0.30	5.45	0.17	20.52	18.90	15.95	20.34	9.91	8.08	5.79	9.73								

Note

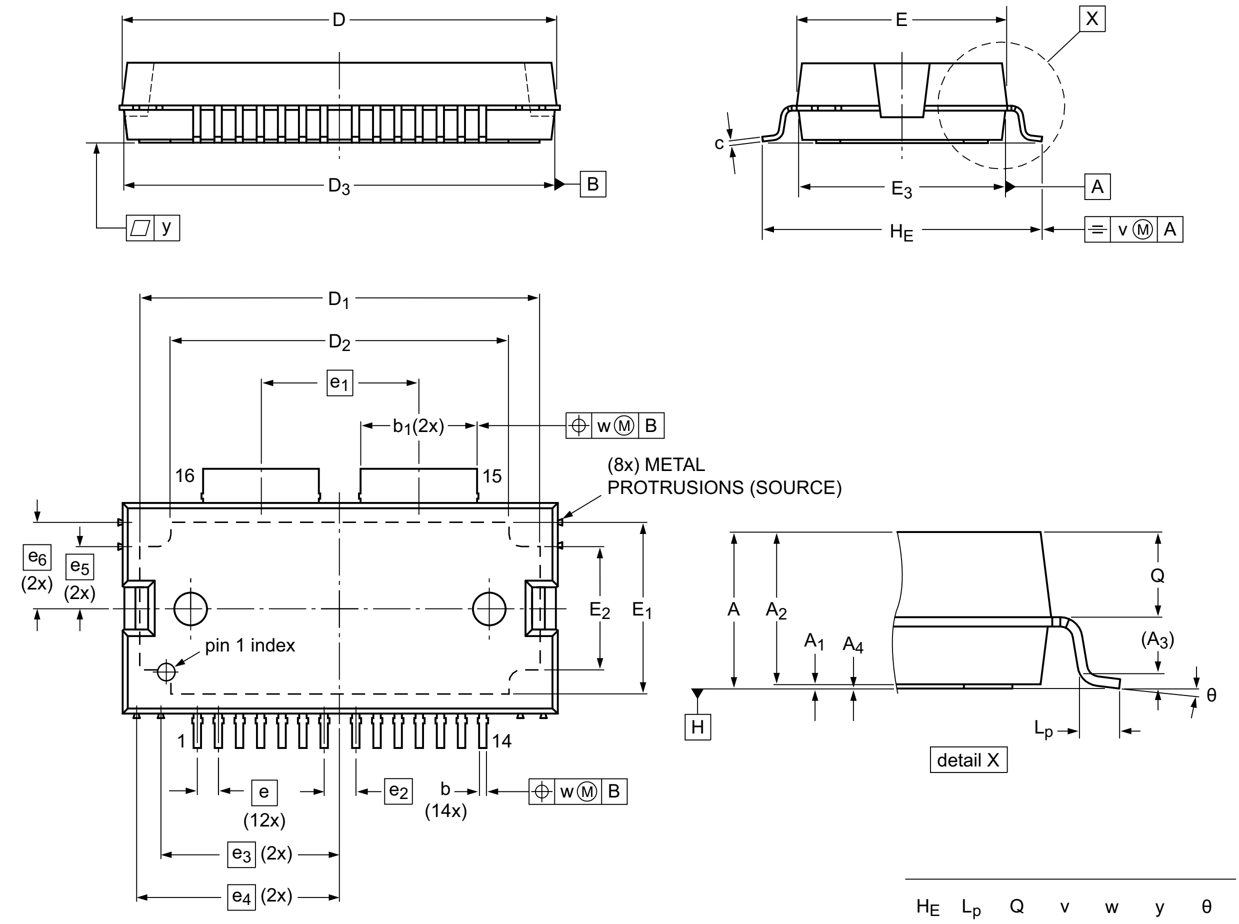
1. Package body dimensions “D and “E do not include mold and metal protrusions. Allowable protrusion is 0.25 mm per side.
2. Lead width dimensions “b and “ b_1 do not include dambar protrusions. Allowable dambar protrusion is 0.25 mm in total per lead.

sot1211-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1211-2						~~15-01-06~~ 15-01-12

Fig 16. Package outline SOT1211-2 (HSOP16F)

HSOP16: plastic, heatsink small outline package; 16 leads **SOT1212-2**



0 10 mm
scale

Dimensions (mm are the original dimensions)

H_E	L_p	Q	v	w	y	θ
13.5	1.10	2.07				7°
13.2	0.95	2.02	0.25	0.25	0.1	3°
12.9	0.80	1.97				0°

Unit		A	A_1	A_2	A_3	A_4	b	b_1	c	$D^{(1)}$	D_1	D_2	D_3	$E^{(1)}$	E_1	E_2	E_3	e	e_1	e_2	e_3	e_4	e_5	e_6
mm	max	3.9	0.2	3.65		0.06	0.40	5.55	0.27	20.62	19.00	16.05	20.44	10.01	8.18	5.89	9.83							
	nom		0.1	3.60	0.35	0	0.35	5.50	0.22	20.57	18.95	16.00	20.39	9.96	8.13	5.84	9.78	1.0	7.45	1.5	8.45	9.55	2.97	4.07
	min		0	3.55		-0.02	0.30	5.45	0.17	20.52	18.90	15.95	20.34	9.91	8.08	5.79	9.73							

Note

1. Package body dimensions “D" and `E" do not include mold and metal protrusions. Allowable protrusion is 0.25 mm per side.
2. Lead width dimensions `b" and `b1" do not include dambar protrusions. Allowable dambar protrusion is 0.25 mm in total per lead.
3. Dimension A_4 is measured with respect to bottom of the heatsink DATUM H. Positive value means that the bottom of the heatsink is higher than the bottom of the lead.

sot1212-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1212-2						~~14-12-08~~ 15-01-14

Fig 17. Package outline SOT1212-2 (HSOP16)

10. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

11. Abbreviations

Table 11. Abbreviations

Acronym	Description
AM	Amplitude Modulation
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN8	Eighth Generation
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
PM	Phase Modulation
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM8G0710S-30PB_S-30PBG v.2	20150701	Product data sheet	-	BLM8G0710S-30PB_ S-30PBG v.1
Modifications:	• Table 3 on page 3: the package version of the BLM7G0710S-30PB has been changed to SOT1211-2 • Table 3 on page 3: the package version of the BLM7G0710S-30PBG has been changed to SOT1212-2 • Figure 16 on page 14: the figure now shows the SOT1211-2 package outline • Figure 17 on page 15: the figure now shows the SOT1212-2 package outline			
BLM8G0710S-30PB_S-30PBG v.1	20150123	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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15. Contents

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